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2SC4417**Silicon NPN epitaxial planar type**

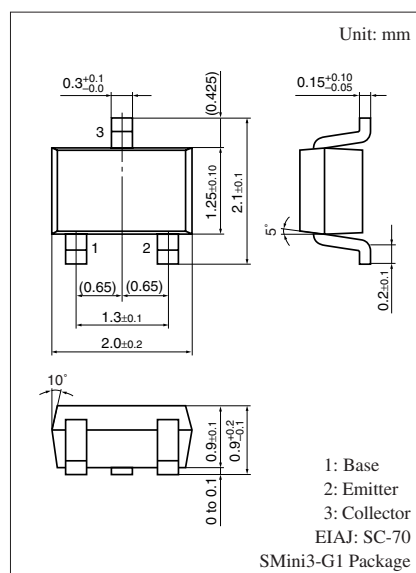
For intermediate frequency amplification of TV image

■ Features

- High transition frequency f_T
- Satisfactory linearity of forward current transfer ratio h_{FE}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	45	V
Collector-emitter voltage (Base open)	V_{CEO}	35	V
Emitter-base voltage (Collector open)	V_{EBO}	4	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



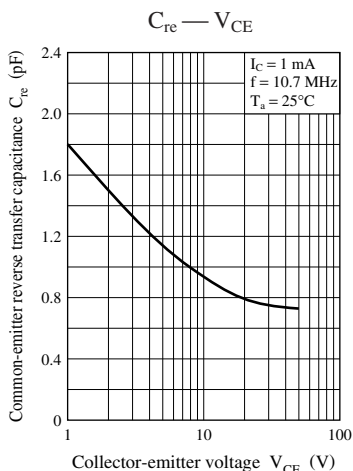
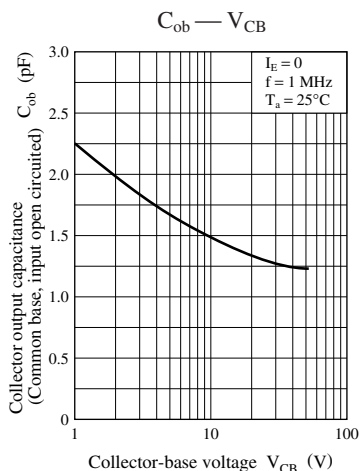
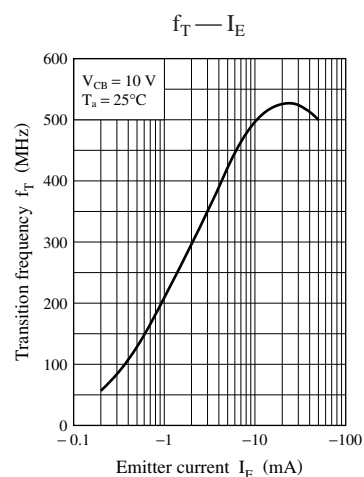
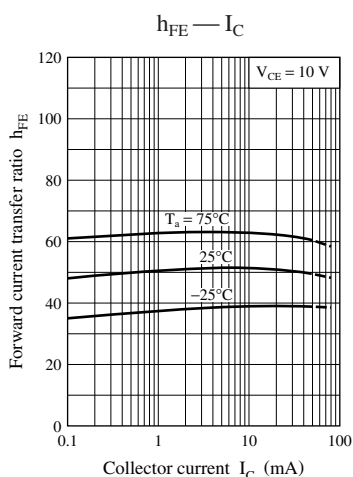
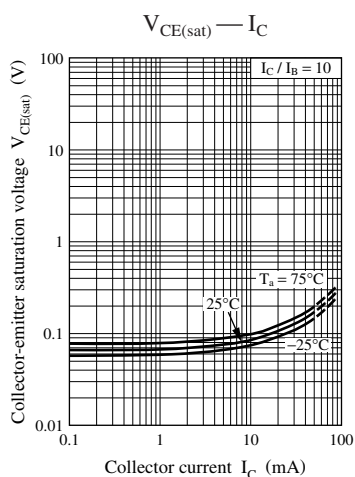
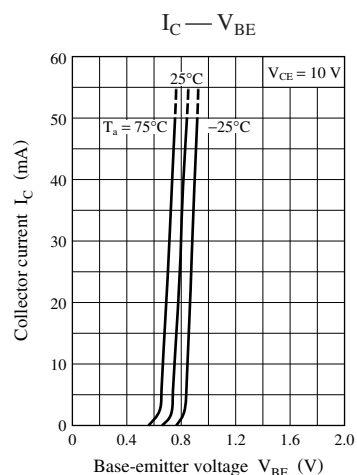
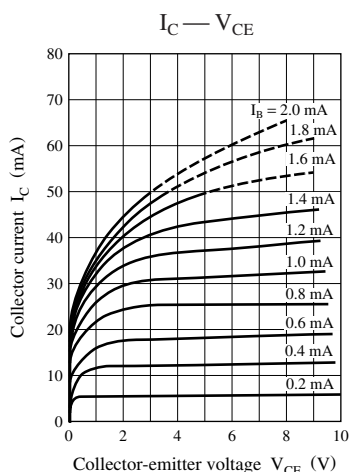
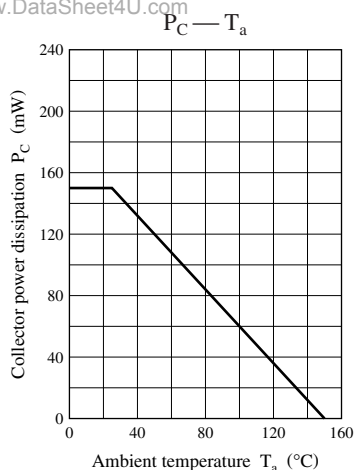
Marking Symbol: 2Z

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10\ \mu\text{A}$, $I_E = 0$	45			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1\ \text{mA}$, $I_B = 0$	35			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu\text{A}$, $I_C = 0$	4			V
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 20\ \text{V}$, $I_B = 0$			10	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 10\ \text{mA}$	20		100	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20\ \text{mA}$, $I_B = 2\ \text{mA}$			0.5	V
Transition frequency *	f_T	$V_{CB} = 10\ \text{V}$, $I_E = -10\ \text{mA}$, $f = 200\ \text{MHz}$		500		MHz
Common-emitter reverse transfer capacitance	C_{re}	$V_{CB} = 10\ \text{V}$, $I_E = -1\ \text{mA}$, $f = 10.7\ \text{MHz}$			1.5	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement



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